

N- and P-Channel 20V (D-S) Power MOSFET

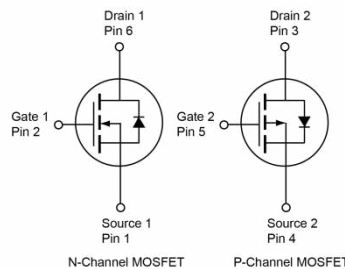
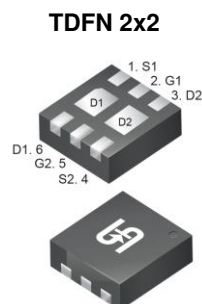
FEATURES

- Low $R_{DS(ON)}$ to minimize conductive losses
- Low gate charge for fast power switching
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Load Switch
- Power Management
- Portable Devices

KEY PERFORMANCE PARAMETERS			
PARAMETER	TYPE	VALUE	UNIT
V_{DS}	N-ch	20	V
	P-ch	-20	
$R_{DS(on)}$ (max)	N-ch	$V_{GS} = 4.5V$	40
		$V_{GS} = 2.5V$	47
		$V_{GS} = 1.8V$	54
	P-ch	$V_{GS} = -4.5V$	70
		$V_{GS} = -2.5V$	100
		$V_{GS} = -1.8V$	110
Q_g	N-ch	7.5	nC
	P-ch	9.4	



Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)				
PARAMETER	SYMBOL	N-ch	P-ch	UNIT
Drain-Source Voltage	V_{DS}	20	-20	V
Gate-Source Voltage	V_{GS}	± 10	± 10	V
Continuous Drain Current (Note 1)	I_D	$T_C = 25^\circ C$	10	-8
		$T_A = 25^\circ C$	5.5	-4.4
Pulsed Drain Current	I_{DM}	40	-32	A
Total Power Dissipation	P_D	$T_C = 25^\circ C$	5	5
		$T_C = 125^\circ C$	1	1
Total Power Dissipation	P_D	$T_A = 25^\circ C$	1.89	1.89
		$T_A = 125^\circ C$	0.38	0.38
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150		$^\circ C$

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Thermal Resistance – Junction to Case	$R_{\theta JC}$	25	$^\circ C/W$
Thermal Resistance – Junction to Ambient	$R_{\theta JA}$	66	

Thermal Performance Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)							
PARAMETER	CONDITIONS	SYMBOL	TYPE	MIN	TYP	MAX	UNIT
Static							
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu\text{A}$	BV_{DSS}	N-ch	20	--	--	V
	$V_{GS} = 0V, I_D = -250\mu\text{A}$		P-ch	-20	--	--	
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	N-ch	0.4	0.6	0.8	V
	$V_{GS} = V_{DS}, I_D = -250\mu\text{A}$		P-ch	-0.4	-0.6	-0.8	
Gate-Source Leakage Current	$V_{GS} = \pm 10V, V_{DS} = 0V$	I_{GSS}	N-ch	--	--	± 100	nA
	$V_{GS} = \pm 10V, V_{DS} = 0V$		P-ch	--	--	± 100	
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$	I_{DSS}	N-ch	--	--	1	μA
	$V_{GS} = 0V, V_{DS} = 20V$ $T_J = 125^\circ\text{C}$			--	--	100	
	$V_{GS} = 0V, V_{DS} = -20V$		P-ch	--	--	-1	
	$V_{GS} = 0V, V_{DS} = -20V$ $T_J = 125^\circ\text{C}$			--	--	-100	
Drain-Source On-State Resistance ^(Note 2)	$V_{GS} = 4.5V, I_D = 5.5A$	$R_{DS(on)}$	N-ch	--	27	40	m Ω
	$V_{GS} = 2.5V, I_D = 5A$			--	34	47	
	$V_{GS} = 1.8V, I_D = 3.9A$			--	48	54	
	$V_{GS} = -4.5V, I_D = -4.4A$		P-ch	--	47	70	
	$V_{GS} = -2.5V, I_D = -4A$			--	66	100	
	$V_{GS} = -1.8V, I_D = -3.9A$			--	102	110	
Forward Transconductance ^(Note 2)	$V_{DS} = 5V, I_D = 5.5A$	g_{fs}	N-ch	--	19	--	S
	$V_{DS} = -5V, I_D = -4.4A$		P-ch	--	11	--	
Dynamic ^(Note 3)							
Total Gate Charge	N-ch $V_{GS} = 4.5V,$ $V_{DS} = 10V, I_D = 5.5A$	Q_g	N-ch	--	7.5	--	nC
			P-ch	--	9.4	--	
Gate-Source Charge	P-ch	Q_{gs}	N-ch	--	0.65	--	
			P-ch	--	1.63	--	
Gate-Drain Charge	$V_{GS} = -4.5V,$ $V_{DS} = -10V, I_D = -4.4A$	Q_{gd}	N-ch	--	2	--	
			P-ch	--	2	--	
Input Capacitance	N-ch $V_{GS} = 0V, V_{DS} = 10V$	C_{iss}	N-ch	--	534	--	pF
			P-ch	--	909	--	
Output Capacitance	f = 1.0MHz P-ch	C_{oss}	N-ch	--	82	--	
			P-ch	--	105	--	
Reverse Transfer Capacitance	$V_{GS} = 0V, V_{DS} = -10V$ f = 1.0MHz	C_{rss}	N-ch	--	64	--	
			P-ch	--	90	--	
Gate Resistance	f = 1.0MHz	R_g	N-ch	--	0.69	--	Ω
			P-ch	--	14.9	--	

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)							
PARAMETER	CONDITIONS	SYMBOL	TYPE	MIN	TYP	MAX	UNIT
Switching (Note 3)							
Turn-On Delay Time	N-ch	$t_{d(on)}$	N-ch	--	8.7	--	ns
			P-ch	--	11.5	--	
Turn-On Rise Time	$V_{GS} = 4.5\text{V}, R_G = 2\Omega$ $V_{DS} = 10\text{V}, I_D = 5.5\text{A}$	t_r	N-ch	--	72	--	
			P-ch	--	65.2	--	
Turn-Off Delay Time	P-ch	$t_{d(off)}$	N-ch	--	24.5	--	
			P-ch	--	39.8	--	
Turn-Off Fall Time	$V_{DS} = -10\text{V}, I_D = -4.4\text{A}$	t_f	N-ch	--	88.8	--	
			P-ch	--	85.6	--	
Source-Drain Diode							
Forward Voltage (Note 2)	$V_{GS} = 0\text{V}, I_S = 5.5\text{A}$	V_{SD}	N-ch	--	0.9	--	V
	$V_{GS} = 0\text{V}, I_S = -4.4\text{A}$		P-ch	--	-0.87	--	
Reverse recovery Time	N-ch $I_S = 5.5\text{A},$ $dI/dt = 100\text{A}/\mu\text{s}$	t_{rr}	N-ch	--	11.7	--	nc
			P-ch	--	12.9	--	
Reverse Recovery Charge	P-ch $I_S = -4.4\text{A},$ $dI/dt = 100\text{A}/\mu\text{s}$	Q_{rr}	N-ch	--	4.73	--	nc
			P-ch	--	5.13	--	

Notes:

1. Silicon limited current only.
2. Pulse test: Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. Switching time is essentially independent of operating temperature.

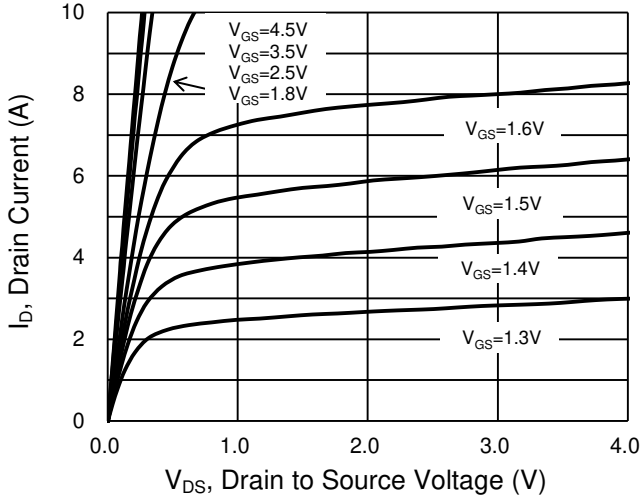
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM2538CQ RFG	TDFN 2x2	3,000pcs / 7" Reel

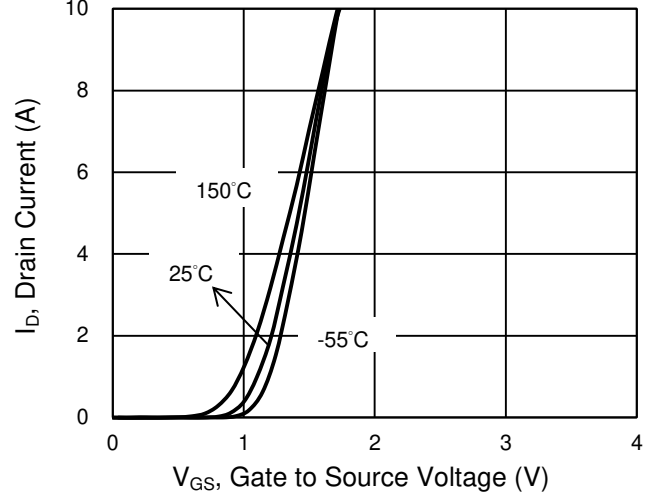
CHARACTERISTICS CURVES (N-Channel)

($T_A = 25^\circ\text{C}$ unless otherwise noted)

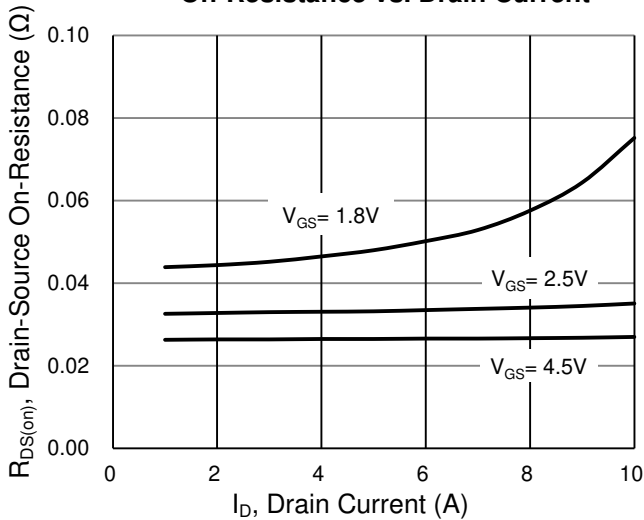
Output Characteristics



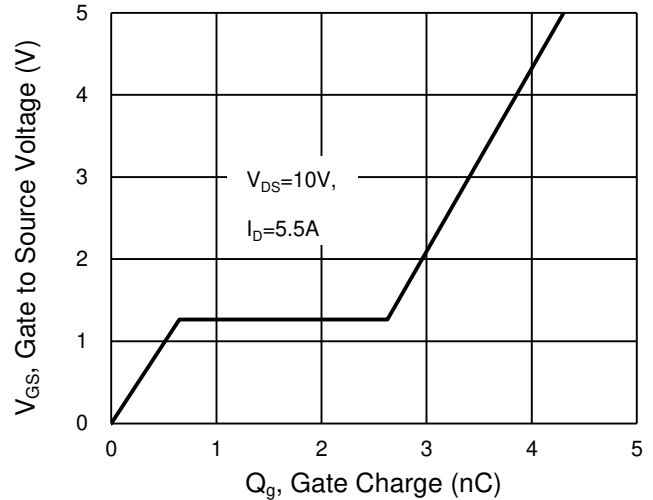
Transfer Characteristics



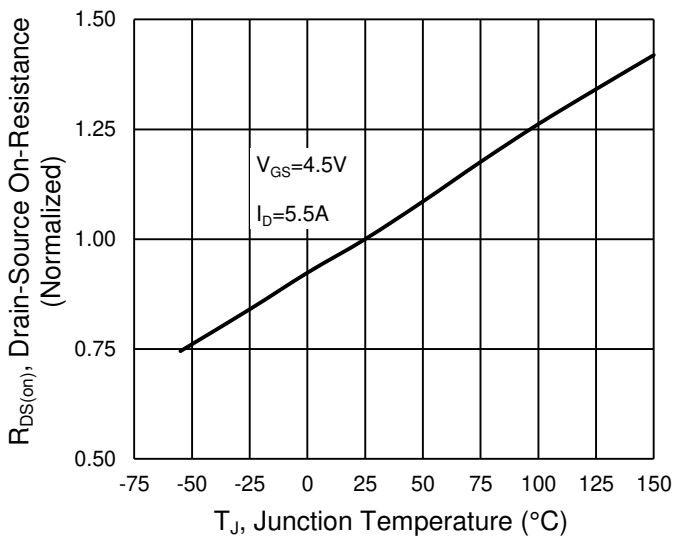
On-Resistance vs. Drain Current



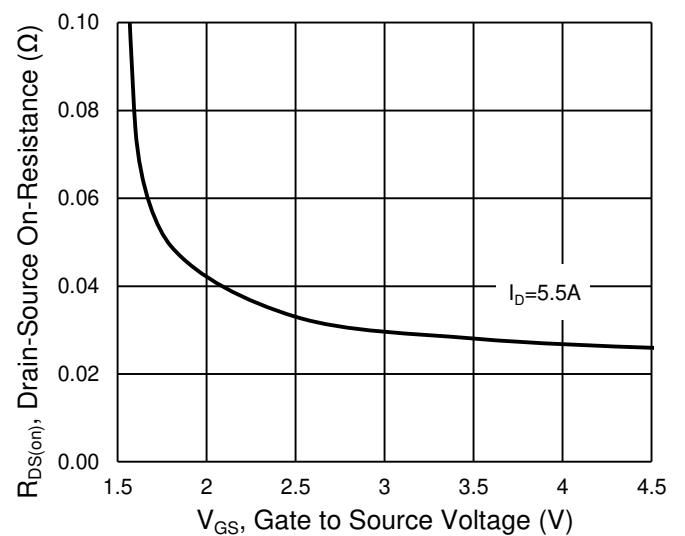
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



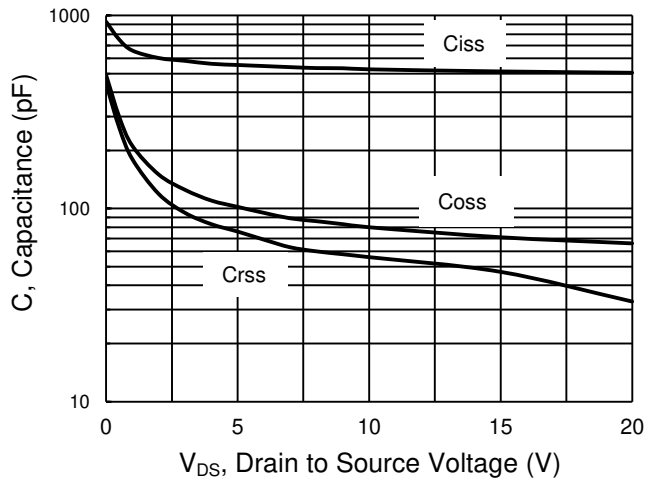
On-Resistance vs. Gate-Source Voltage



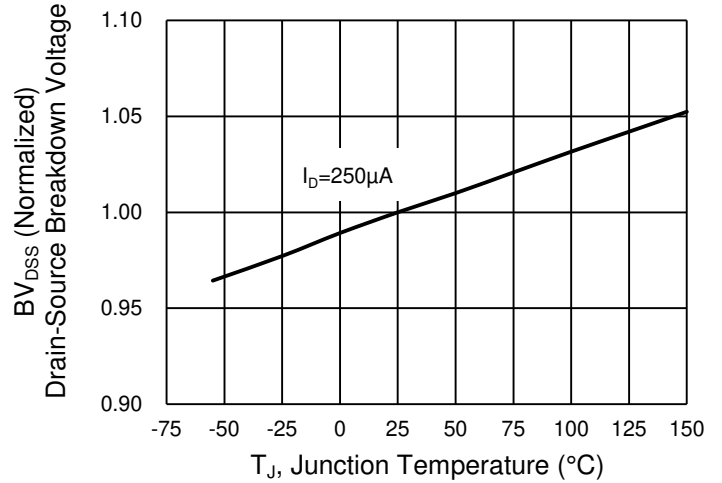
CHARACTERISTICS CURVES (N-Channel)

($T_A = 25^\circ\text{C}$ unless otherwise noted)

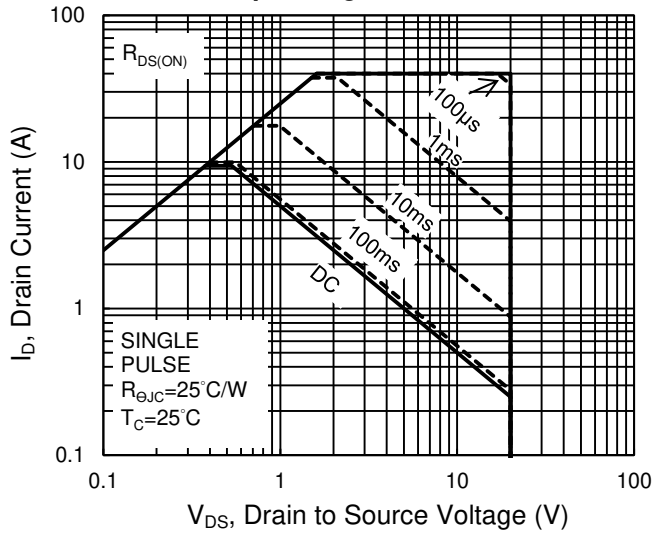
Capacitance vs. Drain-Source Voltage



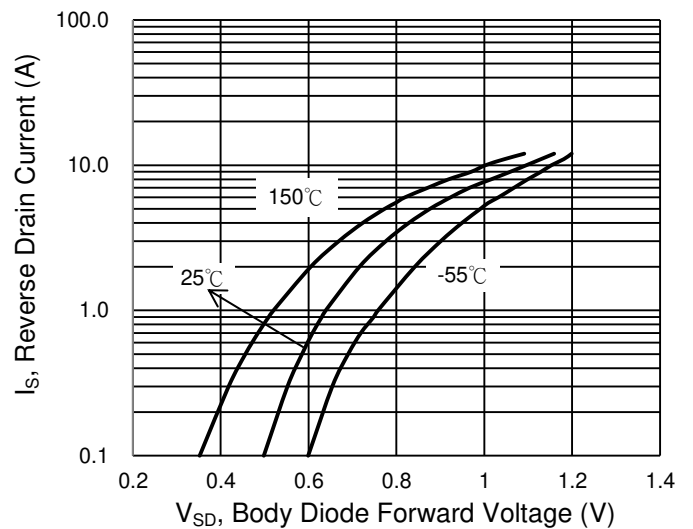
BV_{DSS} vs. Junction Temperature



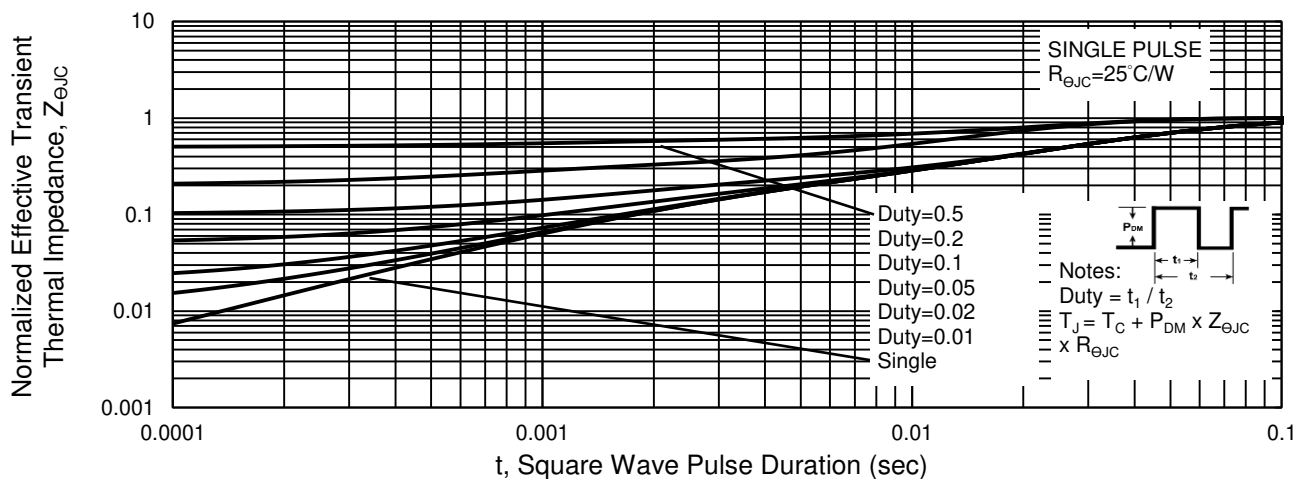
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage



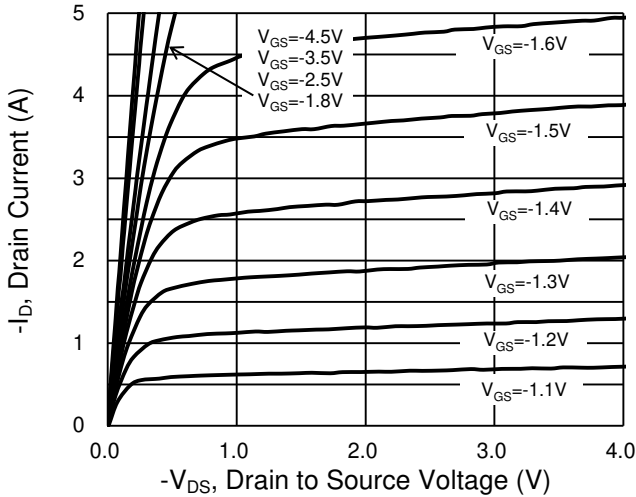
Normalized Thermal Transient Impedance, Junction-to-Case



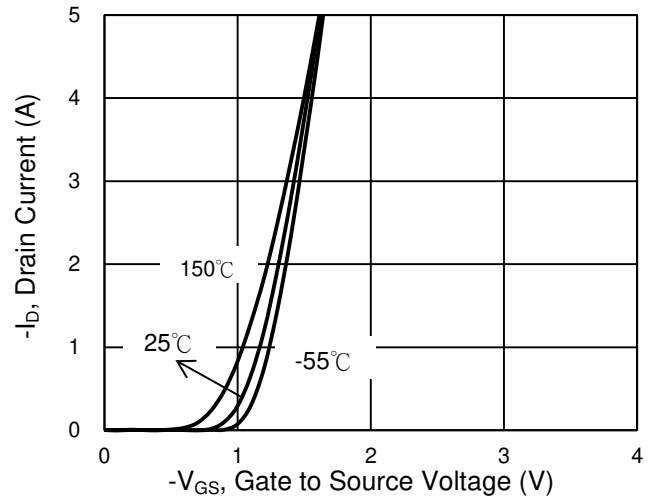
CHARACTERISTICS CURVES (P-Channel)

($T_A = 25^\circ\text{C}$ unless otherwise noted)

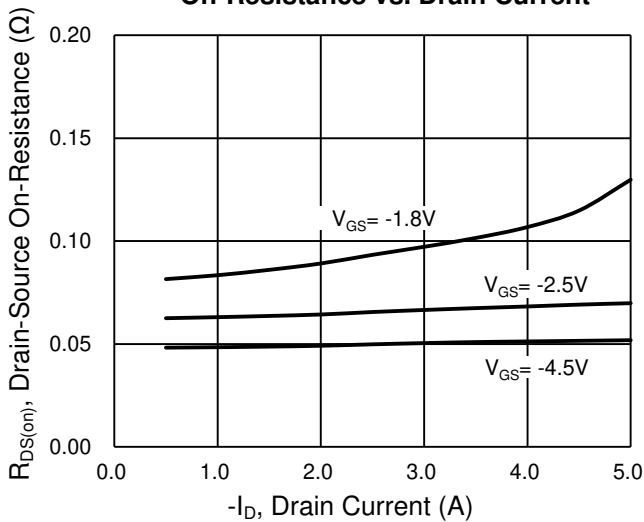
Output Characteristics



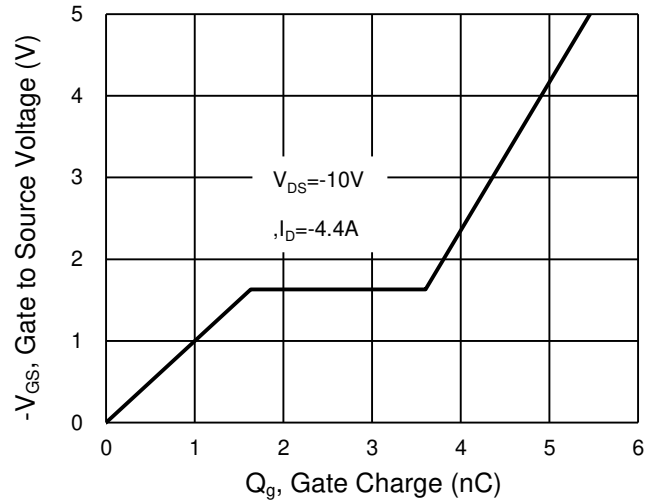
Transfer Characteristics



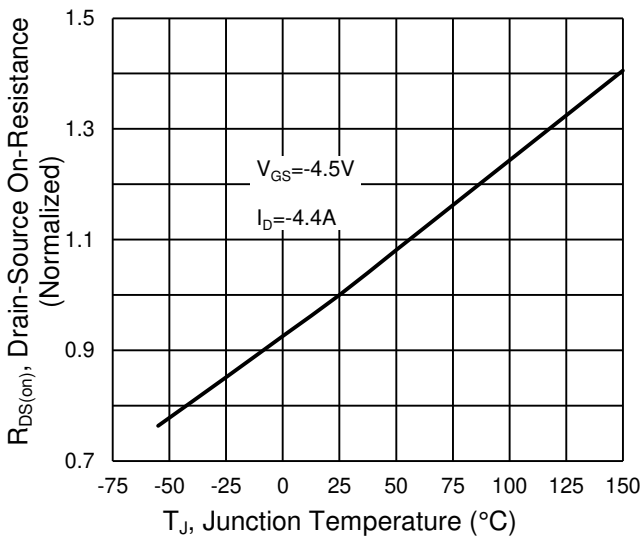
On-Resistance vs. Drain Current



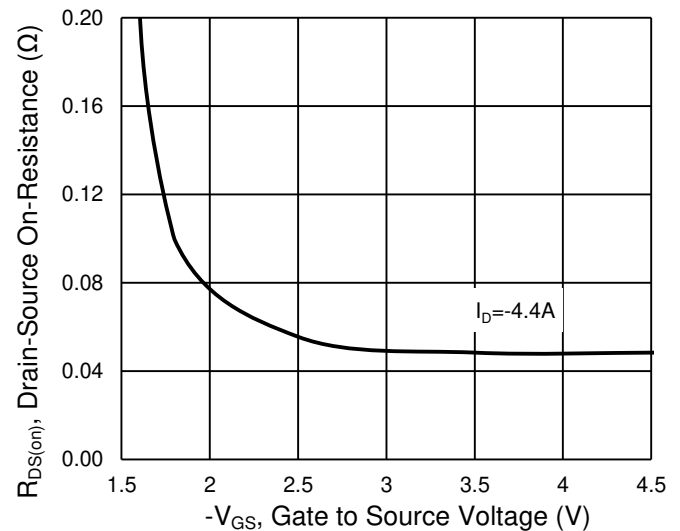
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



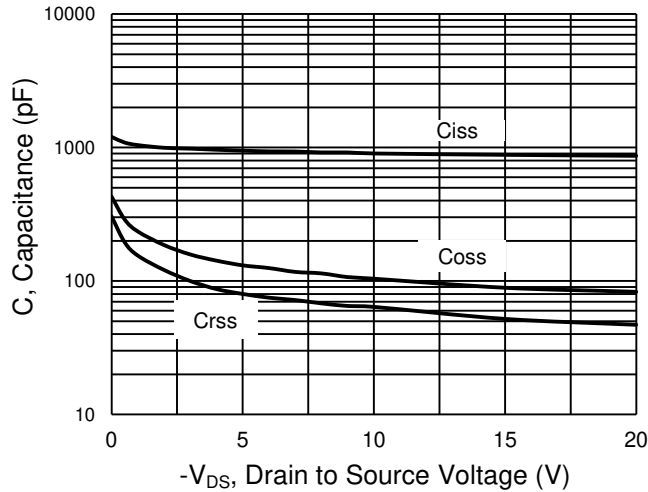
On-Resistance vs. Gate-Source Voltage



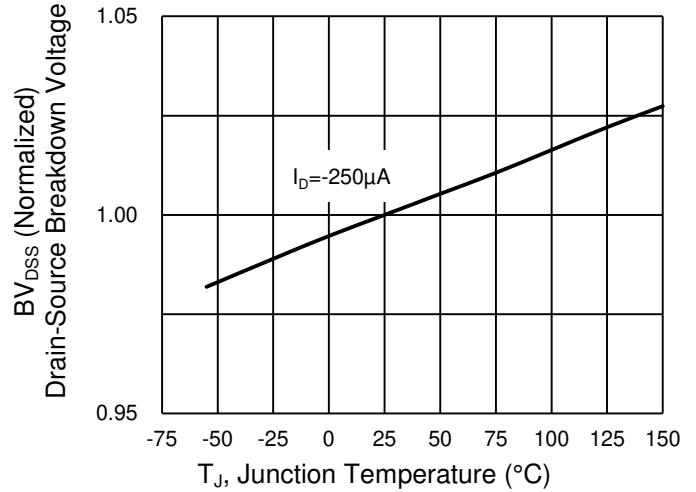
CHARACTERISTICS CURVES (P-Channel)

($T_A = 25^\circ\text{C}$ unless otherwise noted)

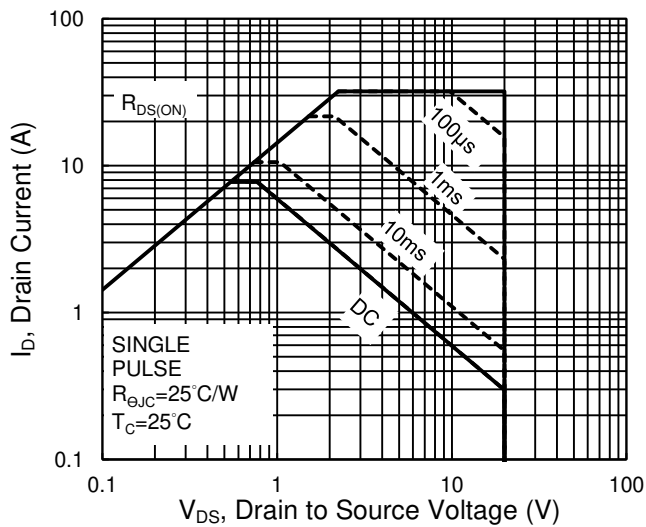
Capacitance vs. Drain-Source Voltage



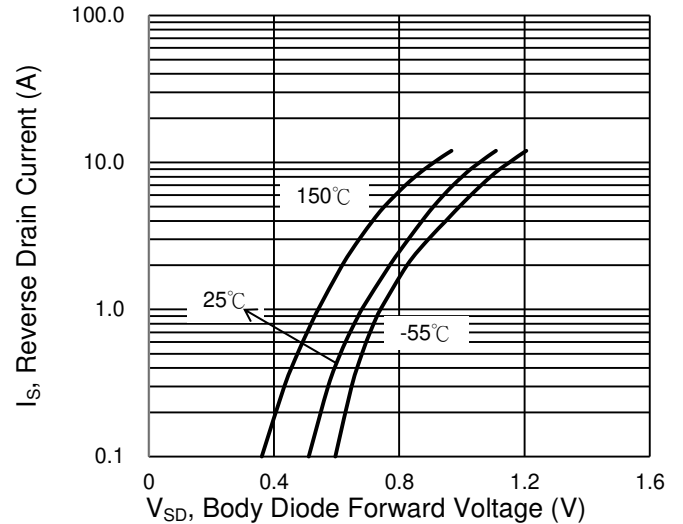
BV_{DSS} vs. Junction Temperature



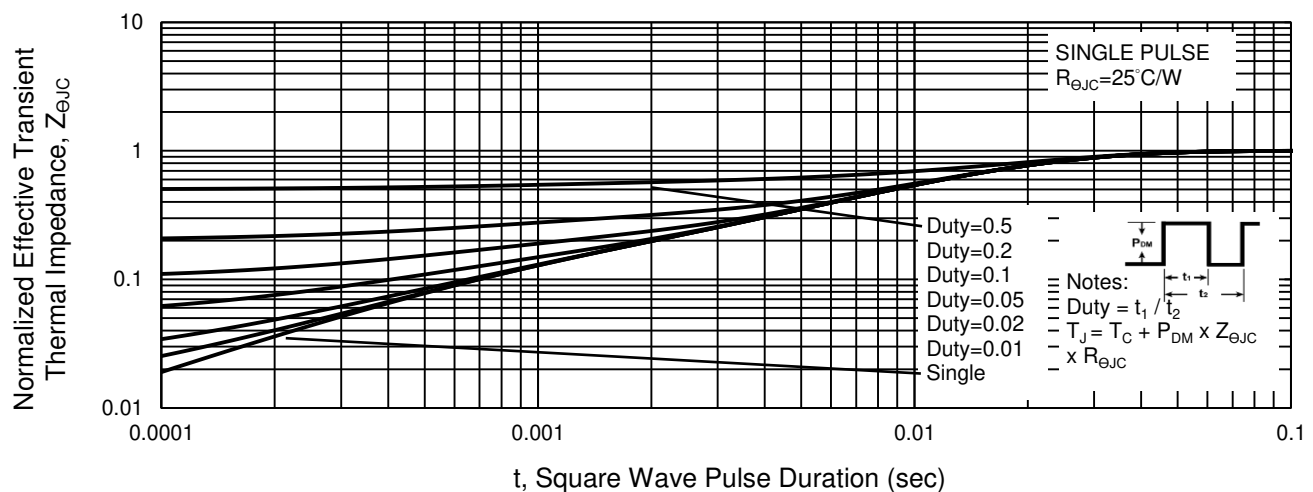
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

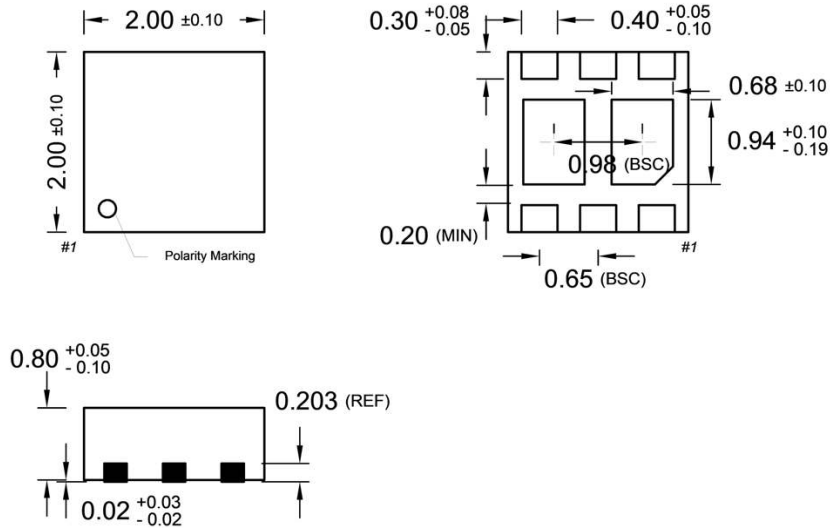


Normalized Thermal Transient Impedance, Junction-to-Case

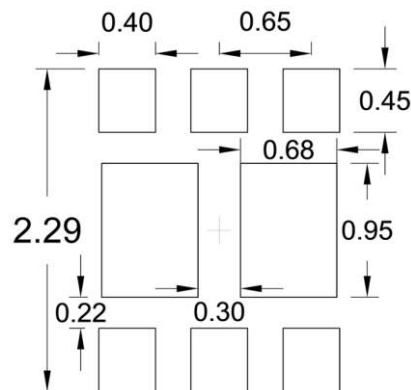


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

TDFN 2x2



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



- Y** = Year Code
- M** = Month Code for Halogen Free
- O** =Jan **P** =Feb **Q** =Mar **R** =Apr
- S** =May **T** =Jun **U** =Jul **V** =Aug
- W** =Sep **X** =Oct **Y** =Nov **Z** =Dec
- L** = Lot Code (1~9, A~Z)

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